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# 30V N-Channel NexFET™ Power MOSFET

## FEATURES

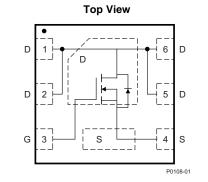
- Optimized for 5V Gate Drive
- Ultra Low Q<sub>q</sub> and Q<sub>qd</sub>
- Low Thermal Resistance
- Pb Free
- RoHS Compliant
- Halogen Free
- SON 2-mm × 2-mm Plastic Package

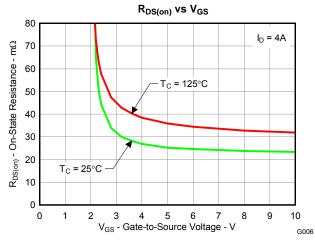
### **APPLICATIONS**

- DC-DC Converters
- Battery and Load Management Applications

## DESCRIPTION

The NexFET power MOSFET has been designed to minimize losses in power conversion applications and optimized for 5V gate drive applications. The 2-mm × 2-mm SON offers excellent thermal performance for the size of the package.





### PRODUCT SUMMARY

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V <sub>DS</sub>	Drain to Source Voltage	30	V	
Qg	Gate Charge Total (4.5V)	2.1	nC	
Q <sub>gd</sub>	Gate Charge Gate to Drain	0.4	nC	
		$V_{GS} = 3V$	31	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	V <sub>GS</sub> = 4.5V 26		mΩ
		V <sub>GS</sub> = 8V 24		mΩ
V <sub>GS(th)</sub>	Threshold Voltage	1.3		V

#### **ORDERING INFORMATION**

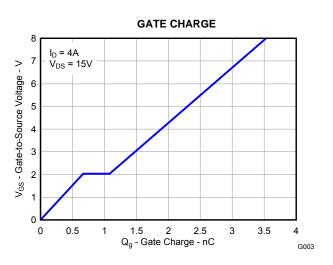
Device	Package	Package Media		Ship
CSD17313Q2	SON 2-mm × 2-mm Plastic Package	13-Inch Reel	3000	Tape and Reel

#### **ABSOLUTE MAXIMUM RATINGS**

$T_{A} = 25^{\circ}$	°C unless otherwise stated	VALUE	UNIT
V <sub>DS</sub>	Drain to Source Voltage	30	V
V <sub>GS</sub>	Gate to Source Voltage	+10 /8	V
	Continuous Drain Current, T <sub>C</sub> = 25°C	5	А
ID	Continuous Drain Current <sup>(1)</sup>	5	А
I <sub>DM</sub>	Pulsed Drain Current, $T_A = 25^{\circ}C^{(2)}$	20	А
PD	Power Dissipation	2.3	W
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C
E <sub>AS</sub>	Avalanche Energy, Single Pulse, $I_D = 19A$ , L = 0.1mH, $R_G = 25\Omega$	18	mJ

(1) Package Limited

(2) Pulse duration ≤300µs, duty cycle ≤2%



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ΔA

## CSD17313Q2





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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## ELECTRICAL CHARACTERISTICS

#### $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Static C	haracteristics	<u>.</u>			
BV <sub>DSS</sub>	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	30		V
I <sub>DSS</sub>	Drain to Source Leakage	$V_{GS} = 0V, V_{DS} = 24V$		1	μA
I <sub>GSS</sub>	Gate to Source Leakage	V <sub>DS</sub> = 0V, V <sub>GS</sub> = +10 / -8V		100	nA
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.9 1.3	1.8	V
		$V_{GS} = 3V$ , $I_D = 4A$	31	42	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = 4.5 V, I_{D} = 4 A$	26	32	mΩ
		$V_{GS} = 8V, I_D = 4A$	24	30	mΩ
9 <sub>fs</sub>	Transconductance	$V_{DS} = 15V, I_{D} = 4A$	16		s
Dynamic	Characteristics				
C <sub>iss</sub>	Input Capacitance		260	340	pF
C <sub>oss</sub>	Output Capacitance	$V_{GS} = 0V, V_{DS} = 15V,$ f = 1MHz	140	180	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		13	17	pF
$R_G$	Series Gate Resistance		1.3	2.6	Ω
Qg	Gate Charge Total (4.5V)		2.1	2.7	nC
Q <sub>gd</sub>	Gate Charge – Gate to Drain	V <sub>DS</sub> = 15V,	0.4		nC
Q <sub>gs</sub>	Gate Charge Gate to Source	$I_D = 4A$	0.7		nC
Q <sub>g(th)</sub>	Gate Charge at Vth		0.3		nC
Q <sub>oss</sub>	Output Charge	$V_{DS} = 13.5V, V_{GS} = 0V$	3.8		nC
t <sub>d(on)</sub>	Turn On Delay Time		2.8		ns
t <sub>r</sub>	Rise Time	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 4.5V,	3.9		ns
t <sub>d(off)</sub>	Turn Off Delay Time	$I_D = 4A, R_G = 2\Omega$	4.2		ns
t <sub>f</sub>	Fall Time		1.3		ns
Diode C	haracteristics				
$V_{SD}$	Diode Forward Voltage	$I_{SD} = 4A, V_{GS} = 0V$	0.85	1	V
Q <sub>rr</sub>	Reverse Recovery Charge	$V_{DD}$ = 13.5V, I <sub>F</sub> = 4A,	6.4		nC
t <sub>rr</sub>	Reverse Recovery Time	di/dt = 300A/µs	12.9		ns

### THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

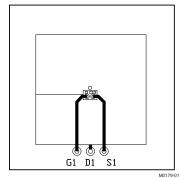
	PARAMETER	MIN	TYP MA	X	UNIT
$R_{ extsf{ heta}JC}$	Thermal Resistance Junction to Case <sup>(1)</sup>		7	.4	°C/W
$R_{\thetaJA}$	Thermal Resistance Junction to Ambient <sup>(1)(2)</sup>			67	°C/W

(1) R<sub>θJC</sub> is determined with the device mounted on a 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch x 1.5-inch (3.81-cm x 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. R<sub>θJC</sub> is specified by design, whereas R<sub>θJA</sub> is determined by the user's board design.
 (2) Device mounted on FR4 material with 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu.

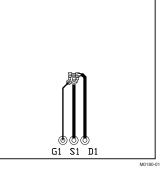


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Max  $R_{\theta JA} = 67^{\circ}C/W$ when mounted on 1 inch<sup>2</sup> (6.45 cm<sup>2</sup>) of 2oz. (0.071-mm thick) Cu.



Max  $R_{\theta,JA} = 228^{\circ}C/W$ when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

#### **TYPICAL MOSFET CHARACTERISTICS**

(T<sub>A</sub> = 25°C unless otherwise stated)

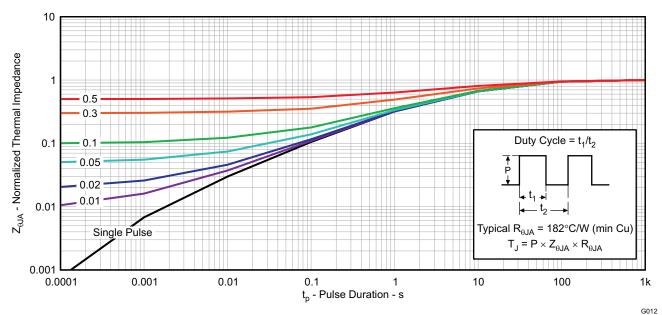


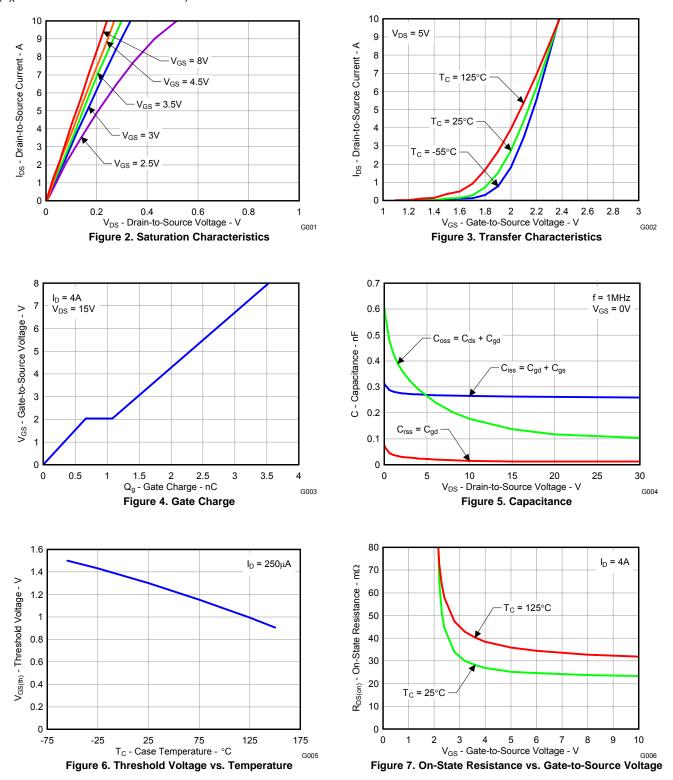
Figure 1. Transient Thermal Impedance

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### **TYPICAL MOSFET CHARACTERISTICS (continued)**

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 



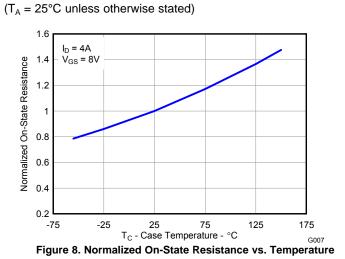




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#### **TYPICAL MOSFET CHARACTERISTICS (continued)**



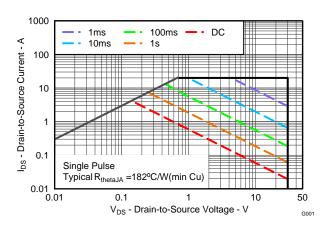
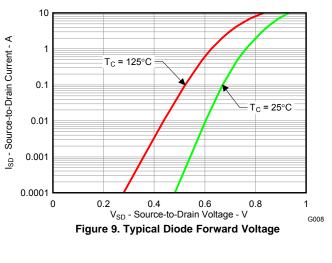


Figure 10. Maximum Safe Operating Area



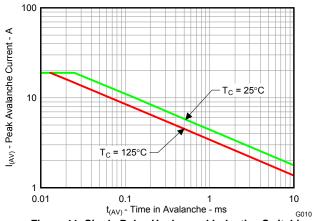
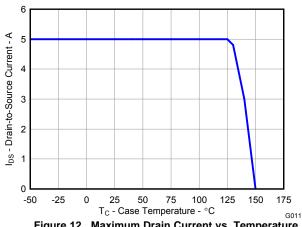


Figure 11. Single Pulse Unclamped Inductive Switching

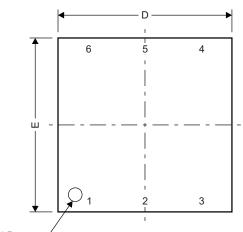


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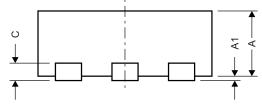
### **MECHANICAL DATA**

## **Q2 Package Dimensions**

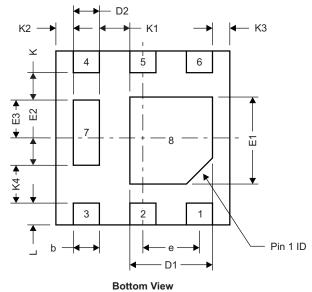








**Front View** 



Pinout					
Source	4, 7				
Gate	3				
Drain	1, 2, 5, 6, 8				

M0175-02

DIM		MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
А	0.700	0.750	0.800	0.028	0.030	0.032	
A1	0.000		0.050	0.000		0.002	
b	0.250	0.300	0.350	0.010	0.012	0.014	
С		0.203 TYP			0.008 TYP		
D		2.000 TYP			0.080 TYP		
D1	0.900	0.950	1.000	0.036	0.038	0.040	
D2		0.300 TYP		0.012 TYP			
E		2.000 TYP		0.080 TYP			
E1	0.900	1.000	1.100	0.036	0.036 0.040		
E2		0.280 TYP		0.0112 TYP			
E3		0.470 TYP		0.0188 TYP			
е		0.650 BSC		0.026 TYP			
К		0.280 TYP			0.0112 TYP		
K1		0.350 TYP		0.014 TYP			
K2		0.200 TYP		0.008 TYP			
K3		0.200 TYP		0.008 TYP			
K4		0.470 TYP		0.0188 TYP			
L	0.200	0.25	0.300	0.008	0.010	0.012	

6

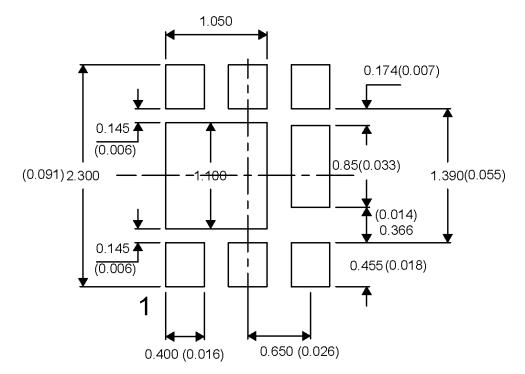


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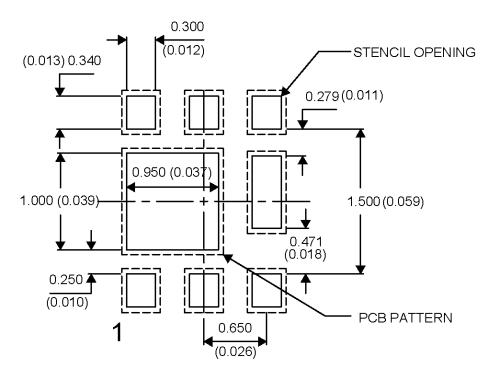
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## **Recommended PCB Pattern**



For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing through PCB Layout Techniques.

#### **Recommended Stencil Pattern**

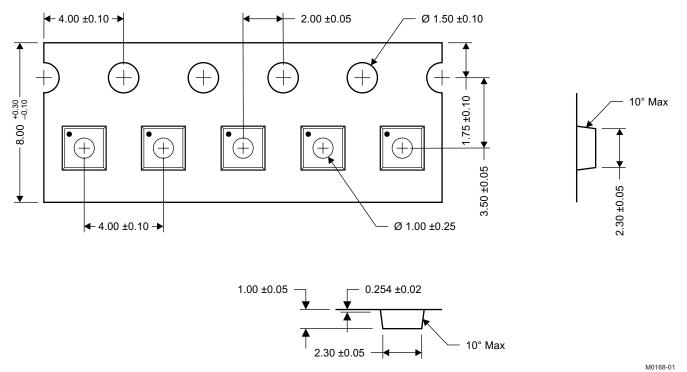


Note: All dimensions are in mm, unless otherwise specified.

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#### **Q2** Tape and Reel Information



- Notes: 1. Measured from centerline of sprocket hole to centerline of pocket
  - 2. Cumulative tolerance of 10 sprocket holes is ±0.20
  - 3. Other material available
  - 4. Typical SR of form tape Max 10<sup>8</sup> OHM/SQ
  - 5. All dimensions are in mm, unless otherwise specified.



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### **REVISION HISTORY**

Changes from Original (March 2010) to Revision A						
Changed Q <sub>rr</sub> - Reverse Recovery Charge From: 10.2 nC To: 6.4 nC						
Changes from Revision A (March 2010) to Revision B	Page					
Deleted the Package Marking Information section						
Changes from Revision B (October 2010) to Revision C	Page					
<ul> <li>Changed the Recommended PCB Pattern</li> <li>Added the Recommended Stencil Pattern</li> </ul>						
Changes from Revision C (January 2013) to Revision D	Page					
Changed Figure 10, Maximum Safe Operating Area						

# PACKAGE MATERIALS INFORMATION

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### TAPE AND REEL INFORMATION





## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions a	are nominal
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Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD17313Q2	WSON	DQK	6	3000	180.0	8.4	2.3	2.3	1.0	4.0	2.3	Q1

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## PACKAGE MATERIALS INFORMATION

10-Apr-2015



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD17313Q2	WSON	DQK	6	3000	550.0	455.0	55.0

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➤ Address :

401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd Minhang District, Shanghai , China

- > Sales :
  - Direct +86 (21) 6401-6692
  - Email amall@ameya360.com
  - QQ 800077892
  - Skype ameyasales1 ameyasales2

# > Customer Service :

Email service@ameya360.com

# > Partnership :

Tel +86 (21) 64016692-8333

Email mkt@ameya360.com